
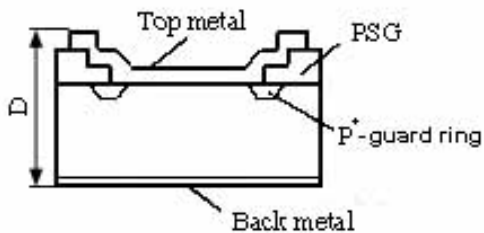
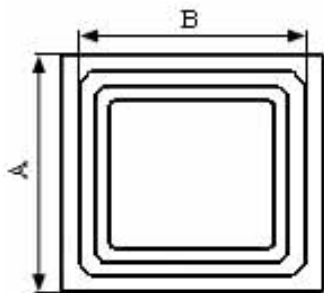


SCHOTTKY DIODES KDN-10020A.
PRELIMINARY



Rev.1. Feb. 2010

 VSP-MIKRON	10A/20V. Die Size-98mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_{BR}	V	20	25
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ $25^{\circ}C, I_F=10,0A$	V_F	V	0,48	0,45
Maximum Reverse Current @ $25^{\circ}C, V_R=25V$ @ $25^{\circ}C, V_R=20V$ @ $125^{\circ}C, V_R=20V$	I_R	mA	- 0,250 160,0	0,250 0,200 150,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	160	-
Peak Repetitive Reverse Surge Current @ $2,0\mu s, f=1kHz., T_J<150^{\circ}C.$	I_{RRM}	A	3,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	± 8 (contact)	
Voltage Rate of Change	dV/dt	V/ μS	10.000	
Operating Junction Temperature	T_J	$^{\circ}C$	150	



DIM	ITEM	μm
A _x A _y	Wafer Form Die Size	2500 2500
B _x B _y	Top Metal Size	2360 2360
D	Thickness	350max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag**; - for Soldering.
Backside metal: **Ti-Ni-Ag**.